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FDMA420NZ

June 2014

# Single N-Channel 2.5V Specified PowerTrench® MOSFET 20V, 5.7A, $30m\Omega$

#### **General Description**

This Single N-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench process to optimize the  $\rm R_{DS}(on)$  @V $_{GS}$ =2.5V on special MicroFET leadframe.

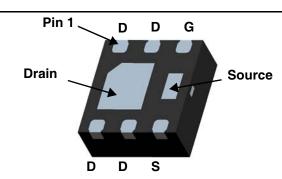
#### **Applications**

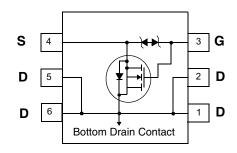
■ Li-Ion Battery Pack



#### **Features**

- $R_{DS(on)} = 30m\Omega$  @  $V_{GS} = 4.5 \text{ V}$ ,  $I_D = 5.7\text{A}$
- $\blacksquare$  R<sub>DS(on)</sub> = 40m $\Omega$  @ V<sub>GS</sub> = 2.5 V, I<sub>D</sub> = 5.0A
- Low Profile-0.8mm maximum-in the new package MicroFET 2x2 mm
- HBM ESD protection level > 2.5kV typical (Note 3)
- Free from halogenated compounds and antimony oxides
- RoHS Compliant





**MicroFET Bottom View 2X2** 

### **Absolute Maximum Ratings** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
$V_{DSS}$	Drain-Source Voltage	20	V	
$V_{GSS}$	Gate-Source Voltage	±12	V	
ı	Drain Current -Continuous	(Note 1a)	5.7	_
ID	-Pulsed		24	1 A
В	Power dissipation (Steady State)	(Note 1a)	2.4	w
$P_{D}$		(Note 1b)	0.9	T **
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C

#### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	52	°C/W
Raia	Thermal Resistance, Junction-to-Ambient	(Note 1b)	145	C/VV

#### **Package Marking and Ordering Information**

Device Marking	Device	Reel Size	Tape Width	Quantity
420	FDMA420NZ	7"	8 mm	3000 units

Max

Тур

Min

Units

## **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

**Parameter** 

Off Char	Off Characteristics							
B <sub>VDSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_{D} = 250\mu A$	20			V		
$\frac{\Delta B_{VDSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C		12		mV/°C		
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V,$			1	μΑ		
I <sub>GSS</sub>	Gate-Body Leakage	$V_{GS} = \pm 12V, \ V_{DS} = 0V$			±10	μΑ		

**Test Conditions** 

#### On Characteristics (Note 2)

Symbol

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6	0.83	1.5	V
$\Delta V_{GS(th)}$ $\Delta T_J$	Gate Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C		-3.1		mV/°C
P Static Prain Source On Posictaneo		$V_{GS} = 4.5V, I_D = 5.7A$		16.8	30	
		$V_{GS} = 4.0V, I_D = 5.7A$		17.3	31	mΩ
	Static Drain-Source On-Resistance	$V_{GS} = 3.1V, I_D = 5.0A$		18.9	33	
R <sub>DS(ON)</sub>	Statio Brain Godroc Chi Hosiotanoc	$V_{GS} = 2.5V$ , $I_D = 5.0A$		21.2	40	11132
		$V_{GS} = 4.5V$ , $I_D = 5.7A$ , $T_J = 150$ °C		24.8	44	
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5V$ , $I_{D} = 5.7A$		28.3		S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 40V V 0V	701	935	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	163	220	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1.01/11/2	125	190	pF
$R_G$	Gate Resistance	f = 1.0MHz	1.92		Ω

#### Switching Characteristics (Note 2)

t <sub>d(on)</sub>	Turn-On Delay Time		9.8	20	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 10V, I_{D} = 1A$	8.6	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 4.5V, R_{GEN} = 6\Omega$	21.5	43	ns
t <sub>f</sub>	Turn-Off Fall Time		8.6	18	ns
$Q_g$	Total Gate Charge	V 10V 1 5.7A	8.8	12	nC
$Q_{gs}$	Gate-Source Charge $V_{DS} = 10V, I_D = 5.7A, V_{GS} = 4.5V$		0.9	2	nC
$Q_{gd}$	Gate-Drain Charge	VGS - 4.5 V	2.4	4	nC

#### **Drain-Source Diode Characteristics and Maximum Ratings**

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current			2.0	Α
$V_{SD}$	Drain-Source Diode Forward Voltage V <sub>GS</sub> = 0V, I <sub>S</sub> = 2.0A		0.69	1.2	V
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> = 5.7A,		20	ns
Q <sub>rr</sub>	Diode Reverse Recovery Charge	di/dt = 100A/μs		5	nC

1. R<sub>0,1/A</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.



a. 52 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



b. 145 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300  $\mu$ s, Duty Cycle < 2.0%.
3. The diode connected between the gate and the source serves only as proection against ESD. No gate overvoltage rating is implied.

#### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

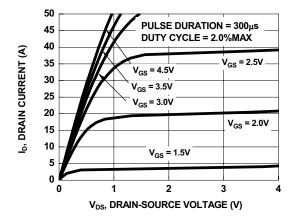


Figure 1. On Region Characteristics

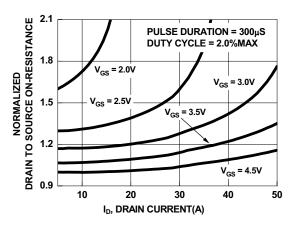


Figure 2. On-Resistance vs Drain Current and Gate Voltage

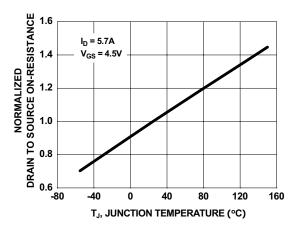


Figure 3. Normalized On Resistance vs Junction Temperature

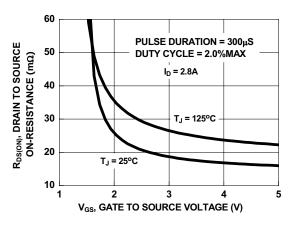


Figure 4. On-Resistance vs Gate to Source Votlage

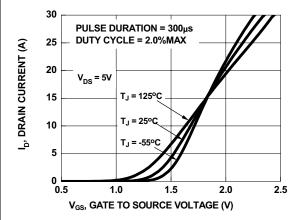


Figure 5. Transfer Characteristics

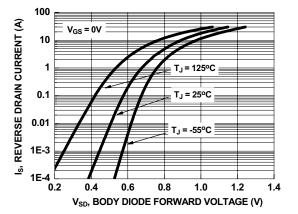
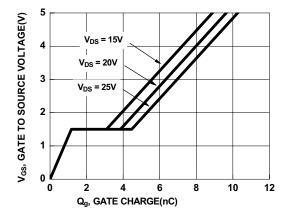


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted



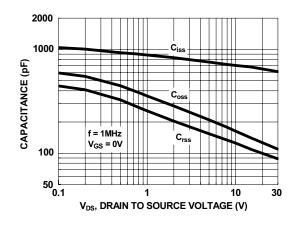
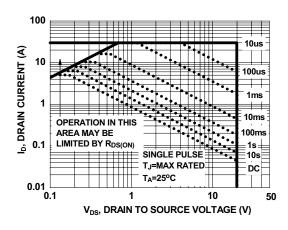


Figure 7. Gate Charge Characteristics

Figure 8. Capacitance vs Drain to Source Voltage



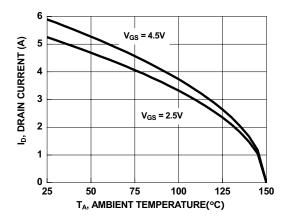


Figure 9. Forward Bias Safe Operating Area

Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

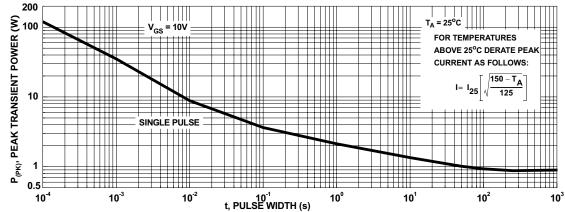


Figure 11. Single Pulse Maximum Power Dissipation

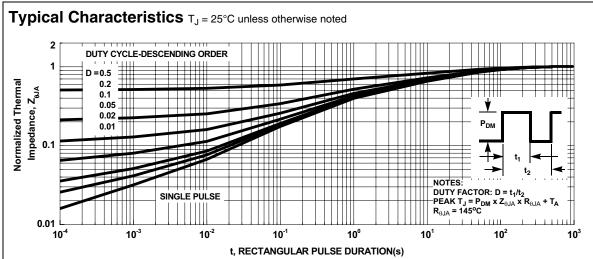
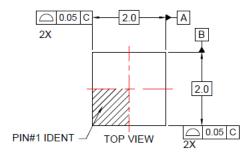
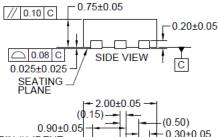


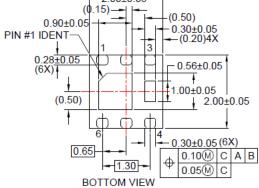
Figure 12. Transient Thermal Response Curve

#### **Preliminary Datasheet**

#### **Dimensional Outline and Pad Layout**

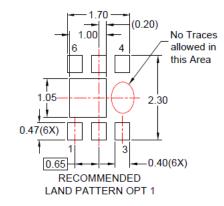


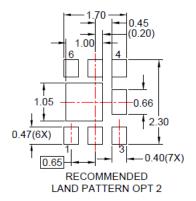




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- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-MLP06Lrev4.







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